

**Features**

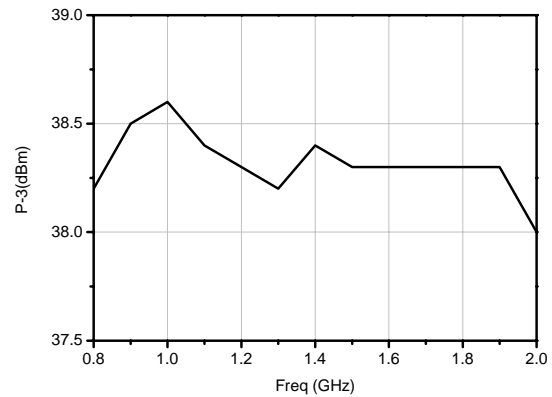
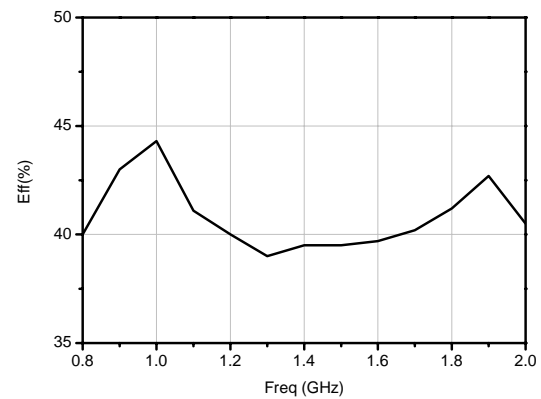
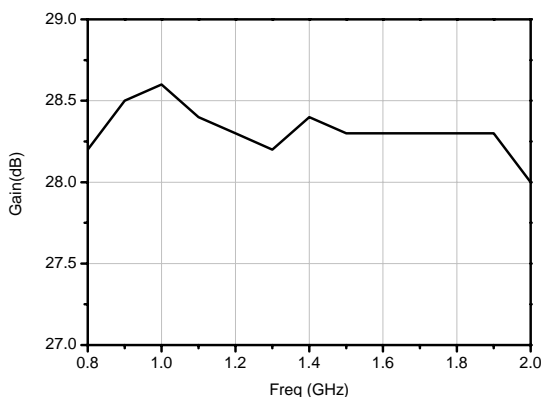
Freq: 0.8~2GHz  
 Power Gain: 28dB  
 Output P<sub>3dB</sub>(P<sub>3dB</sub>): 38dBm  
 PAE@P<sub>3dB</sub>(PAE<sub>3dB</sub>): 40%  
 2<sup>nd</sup>/3<sup>rd</sup> Harmonic: -15dBc  
 Supply Voltage: +28V(V<sub>dd</sub>), -2.4V(V<sub>gg</sub>)  
 Chip Size:24mm×17.4mm×5.5mm

**General Description**

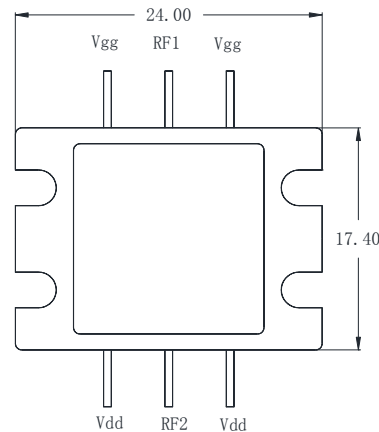
The HG532FC-F07 is an internally-matched GaN HEMT operating between 0.8 and 2GHz. The module has been optimized to provide 28dB gain, 38dBm output power for 3dB compression, and 40% efficiency at P<sub>3dB</sub>.

**Electrical Specifications(T<sub>A</sub>=25 °C, V<sub>dd</sub>= 28V).**

Parameter	Min.	Typ.	Max.
Freq(GHz)	0.8~2		
Gain (dB)	—	28	—
Gain Flatness (dB)	—	±0.5	—
Input VSWR	—	2	—
Output VSWR	—	2	—
P <sub>3dB</sub> (dBm)	—	38	—
PAE <sub>3dB</sub>	—	40%	—
2 <sup>nd</sup> /3 <sup>rd</sup> Harmonic(dBc)	—	-15	—

**Output Power for 3dB Compression**

**PAE@P<sub>3dB</sub>**

**Measured Performance**
**Power Gain**

**Absolute Maximum Ratings**

Supply Voltage	+36V
RF Input Power	+20dBm
Operating Temperature	-55°C ~ 125°C
Storage Temperature	-65°C ~ 150°C

**Outline Drawing (mm)(Package:QF136GC)**


**Notes:**

1. The module should be stored in a dry and nitrogen environment, and used in a clean environment.
2. The pin of the module is brittle, easy to break by external force ,so must be careful when using.
3. The feeder line of the gate and drain need a decoupling capacitor of 10uF, the absolute voltage should not less than 50V.
4. GaN devices are susceptible to damage from electrostatic discharge, proper precautions should be observed in use.